## NSN 5962-01-221-8006

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View Online at https://aerobasegroup.com/nsn/5962-01-221-8006

0.840 inches	
Body Width:	
Between 0.220 inc	hes and 0.310 inches
Body Height:	
0.140 inches	
Maximum Power	Dissipation Rating:
739.0 milliwatts	
Operating Tempu	rature Range:
-55.0 to 125.0 deg	rees celsius
Storage Tempura	ture Range:
-65.0 to 150.0 deg	rees celsius
Features Provide	d:
Schottky and bipol	ar and monolithic and 3-state output and programmable
Inclosure Materia	I:
Ceramic and glass	
Inclosure Configu	iration:
Dual-in-line	
Output Logic For	m:
Transistor-transiste	or logic
Input Circuit Patte	ern:
6 input	
Case Outline Sou	rce And Designator:
D-2 mil-m-38510	
Terminal Surface	Treatment:
Solder	
Voltage Rating A	nd Type Per Characteristic:
7.0 volts power so	burce
Time Rating Per (	Chacteristic:
80.00 nanosecond	s propagation delay time, low to high level output and 80.00 nanoseconds propagation delay time, high to low leve
output	
Memory Device T	уре:
Rom	
Test Data Docum	ent:
96906-mil-std-883	standard (includes industry or association standards, individual manufactureer standards, etc.).
Terminal Type Ar	ad Quantity:
16 printed circuit	
Shelf Life:	
N/a	
Unit Of Measure:	

Yes - demil/mli

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